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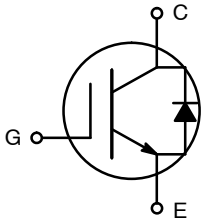
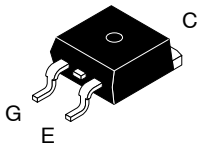
www.onsemi.com

IGBT for Automotive Applications, 650 V, 40 A, D²PAK

AFGB40T65SQDN

BV_{CES}	$V_{CE(sat)}$ TYP	I_C MAX
650 V	1.6 V	160 A





D²PAK–3
CASE 418AJ

Features

- Maximum Junction Temperature: T_J = 175°C
- High Speed Switching Series
- $V_{CE(sat)}$ = 1.6 V (Typ.) @ I_C = 40 A
- 100% of the Part are Dynamically Tested (Note 1)
- AEC−Q101 Qualified
- These Devices are Pb−Free and are RoHS Compliant

Typical Applications

- Automotive On Board Charger
- Automotive DC/DC Converter for HEV

ABSOLUTE MAXIMUM RATINGS

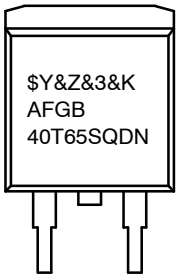
(T_J = 25°C unless otherwise stated)

Parameter	Symbol	Value	Unit
Collector to Emitter Voltage	V_{CES}	650	V
Gate-to-Emitter Voltage	V_{GES}	±20	V
Transient Gate-to-Emitter Voltage	V_{GES}	±30	V
Collector Current – T_C = 25°C	I_C	80	A
Collector Current – T_C = 100°C		40	A
Pulsed Collector Current (Note 2)	I_{CM}	160	A
Diode Forward Current – T_C = 25°C	I_F	40	A
Diode Forward Current – T_C = 100°C		20	A
Pulsed Diode Maximum Forward Current (Note 2)	I_{FM}	160	A
Maximum Power Dissipation – T_C = 25°C	P_D	238	W
Maximum Power Dissipation – T_C = 100°C		119	W
Operating Junction and Storage Temperature	T_J, T_{stg}	−55 to 175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. V_{CC} = 400 V, V_{GE} = 15 V, I_C = 120A, R_G = 100 Ω, Inductive Load.
2. Repetitive rating: pulse width limited by max. Junction temperature.
3. Surface−mounted on FR4 board using 1 in^2 pad size, 1 oz Cu pad.
4. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.

MARKING DIAGRAM



$Y = **onsemi** Logo
&Z = Assembly Plant Code
&3 = 3-Digit Data Code
&K = 2-Digit Lot Traceability Code
AFGB40T65SQDN = Specific Device Code

ORDERING INFORMATION

Device	Package	Shipping†
AFGB40T65SQDN	D²PAK	800 Units / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

THERMAL CHARACTERISTICS

Parameter	Symbol	Max	Unit
Thermal Resistance Junction-to-Case, for IGBT	$R_{\theta JC}$	0.63	°C/W
Thermal Resistance Junction-to-Case, for Diode	$R_{\theta JC}$	1.55	
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	40	

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise stated)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector to Emitter Breakdown Voltage	BV_{CES}	V_{GE} = 0 V, I_C = 1 mA	650	–	–	V
Temperature Coefficient of Breakdown Voltage	$\Delta V_{CES}/\Delta T_J$	I_C = 1 mA, Reference to 25°C	–	0.6	–	V/°C
Collector Cut-Off Current	I_{CES}	V_{CE} = V_{CES}, V_{GE} = 0 V	–	–	250	μA
G–E Leakage Current	I_{GES}	V_{GE} = V_{GES}, V_{CE} = 0 V	–	–	±400	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GE(th)}$	V_{GE} = V_{CE}, I_C = 40 mA	2.6	4.5	6.4	V
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = 40 A, V_{GE} = 15 V, T_C = 25°C	–	1.6	2.1	V
		I_C = 40 A, V_{GE} = 15 V, T_C = 175°C	–	1.92	–	V
DYNAMIC CHARACTERISTIC						
Input Capacitance	C_{ies}	V_{CE} = 30 V, V_{GE} = 0 V, f = 1 MHz	–	2495	–	pF
Output Capacitance	C_{oes}		–	50	–	
Reverse Transfer Capacitance	C_{res}		–	9	–	
SWITCHING CHARACTERISTIC						
Turn-On Delay Time	$t_{d(on)}$	V_{CC}= 400 V, I_C = 40 A, R_G = 6 Ω, V_{GE} = 15 V, Inductive Load, T_C = 25°C	–	17.6	–	ns
Rise Time	t_r		–	19.2	–	ns
Turn-Off Delay Time	$t_{d(off)}$		–	75.2	–	ns
Fall Time	t_f		–	9.6	–	ns
Turn-On Switching Loss	E_{on}		–	0.858	–	mJ
Turn-Off Switching Loss	E_{off}		–	0.229	–	mJ
Total Switching Loss	E_{ts}		–	1.087	–	mJ
Turn-On Delay Time	$t_{d(on)}$	V_{CC}= 400 V, I_C = 40 A, R_G = 6 Ω, V_{GE} = 15 V, Inductive Load, T_C = 175°C	–	16	–	ns
Rise Time	t_r		–	22.4	–	ns
Turn-Off Delay Time	$t_{d(off)}$		–	81.6	–	ns
Fall Time	t_f		–	20.8	–	ns
Turn-On Switching Loss	E_{on}		–	1.14	–	mJ
Turn-Off Switching Loss	E_{off}		–	0.484	–	mJ
Total Switching Loss	E_{ts}		–	1.624	–	mJ
Total Gate Charge	Qg	V_{CE} = 400 V, I_C = 40 A, V_{GE} = 15 V	–	76	–	nC
Gate to Emitter Charge	Qge		–	14	–	nC
Gate to Collector Charge	Qgc		–	17	–	nC

ELECTRICAL CHARACTERISTIC OF THE DIODE (T_J = 25°C unless otherwise stated)

Diode Forward Voltage	VFM	I_F = 20 A	–	1.5	2.1	V

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise stated) (continued)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
ELECTRICAL CHARACTERISTIC OF THE DIODE (T_J = 25°C unless otherwise stated)						
Reverse Recovery Energy	E_{rec}	I_F = 20 A dIF/dt = 200 A/μs, T_C = 25°C	–	22.3	–	μJ
Diode Reverse Recovery Time	t_{rr}		–	131	–	ns
Diode Reverse Recovery Charge	Q_{rr}		–	348	–	nC
Reverse Recovery Energy	E_{rec}	I_F = 20 A dIF/dt = 200A/μs, T_C = 175°C	–	100	–	μJ
Diode Reverse Recovery Time	t_{rr}		–	245	–	ns
Diode Reverse Recovery Charge	Q_{rr}		–	961	–	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

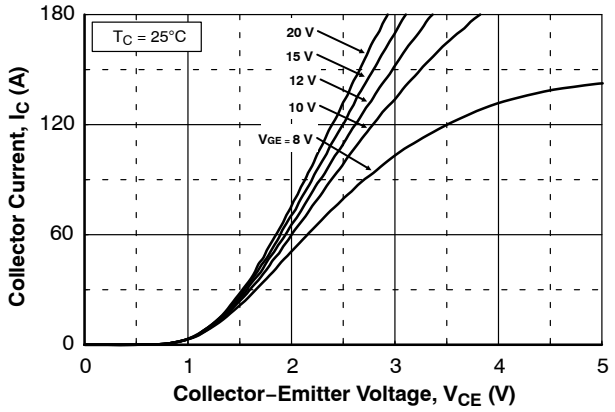


Figure 1. Typical Output Characteristics (25°C)

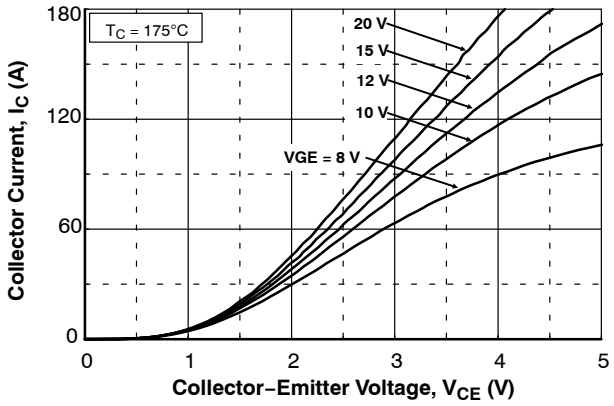


Figure 2. Typical Output Characteristics (175°C)

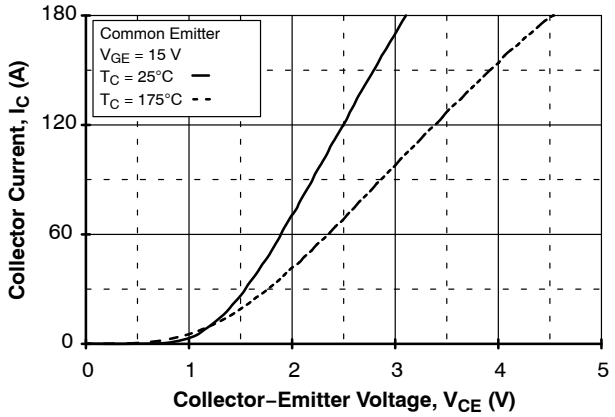


Figure 3. Typical Saturation Voltage Characteristics

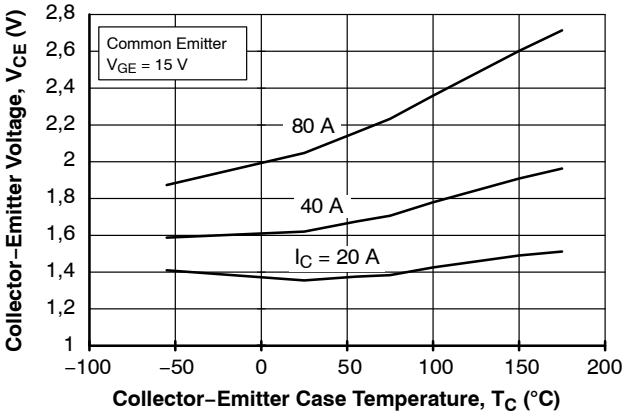


Figure 4. Saturation Voltage vs Case Temperature at Variant Current Level

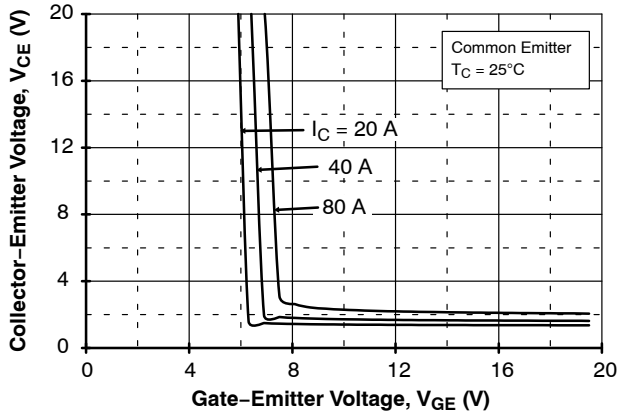


Figure 5. Saturation Voltage vs V_{GE} (25°C)

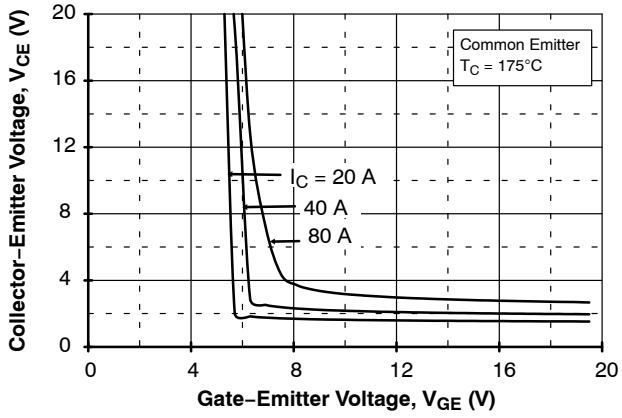


Figure 6. Saturation Voltage vs V_{GE} (175°C)

TYPICAL CHARACTERISTICS

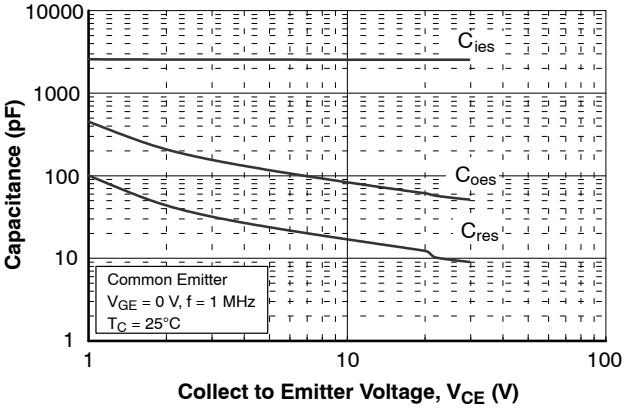


Figure 7. Capacitance Characteristics

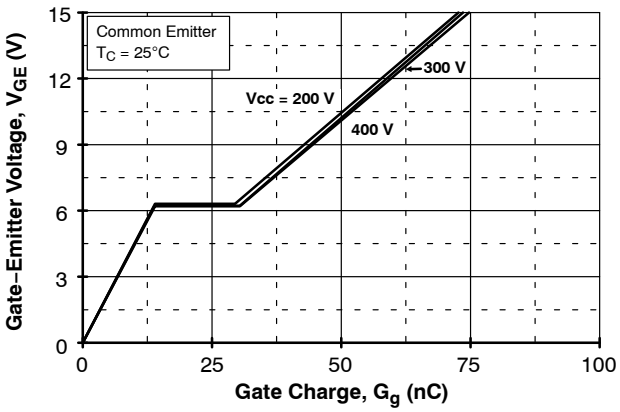


Figure 8. Gate Charge Characteristics

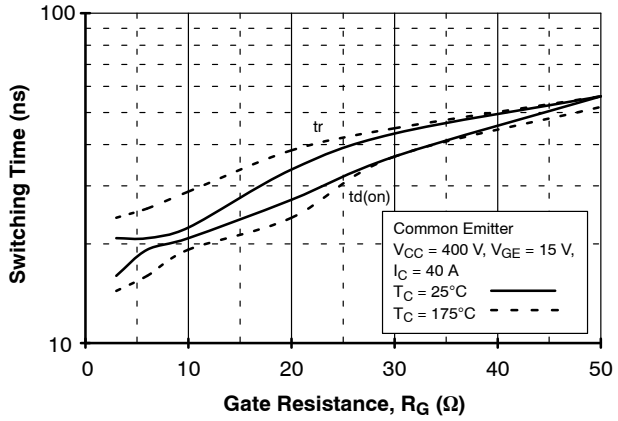


Figure 9. Turn−On Characteristics vs Gate Resistance

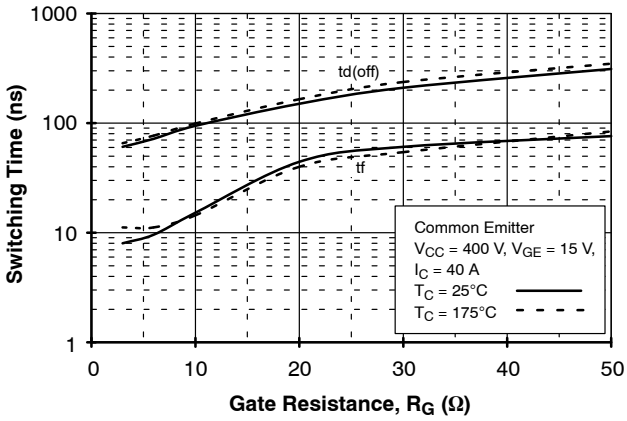


Figure 10. Turn−Off Characteristics vs Gate Resistance

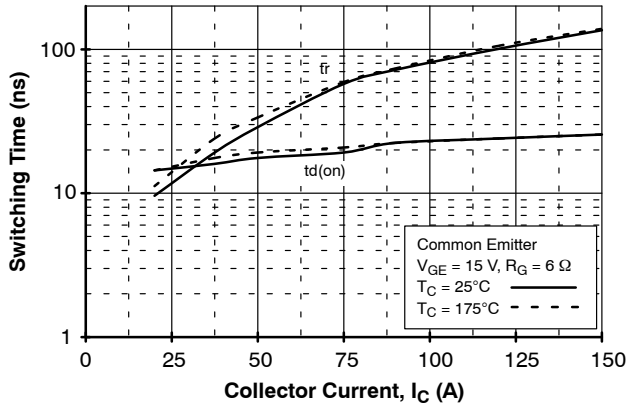


Figure 11. Turn−On Characteristics vs Collector Current

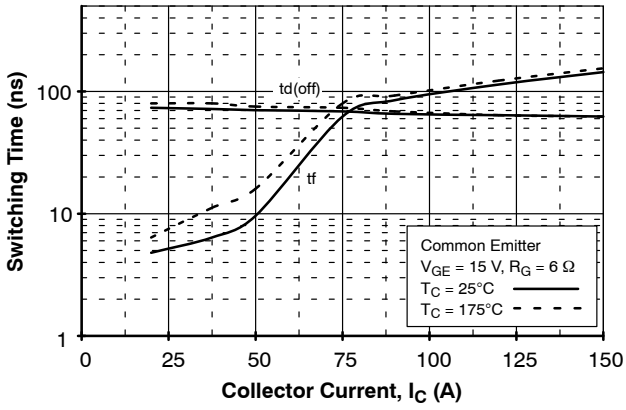


Figure 12. Turn−Off Characteristics vs Collector Current

TYPICAL CHARACTERISTICS

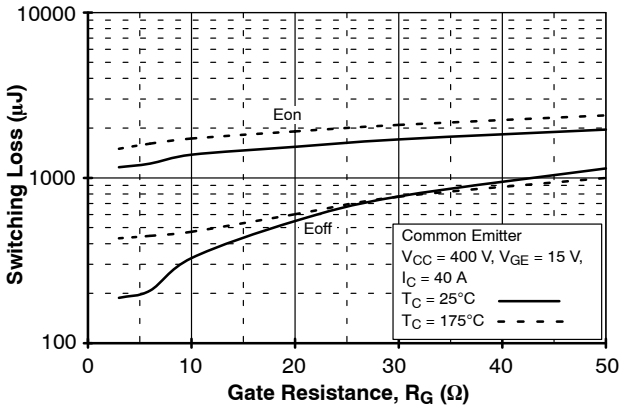


Figure 13. Switching Loss vs Gate Resistance

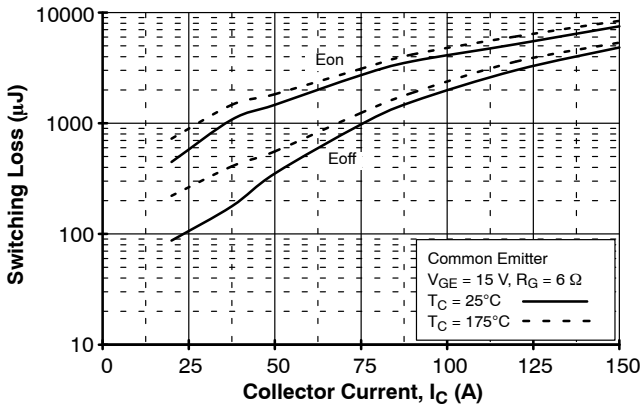


Figure 14. Switching Loss vs Collector Current

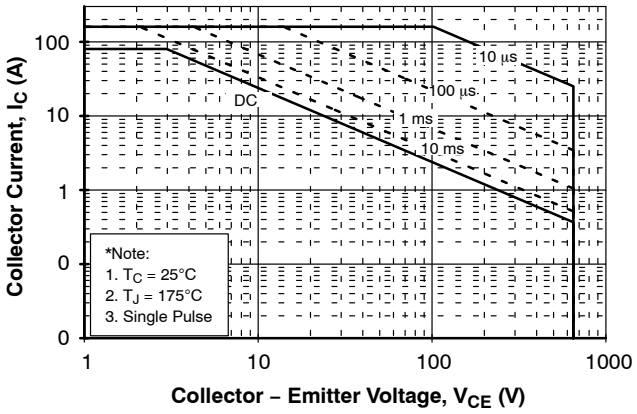


Figure 15. SOA Characteristics

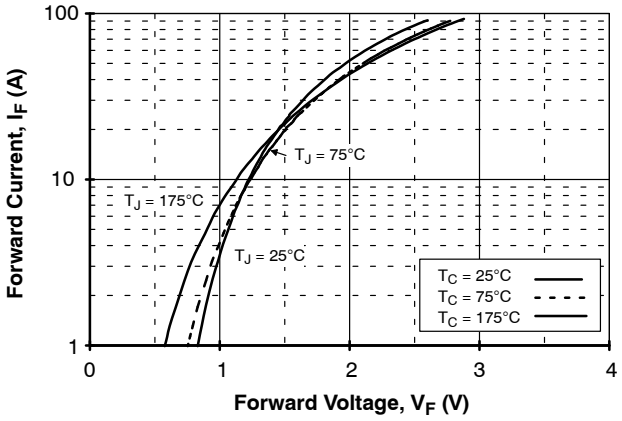


Figure 16. Forward Characteristics

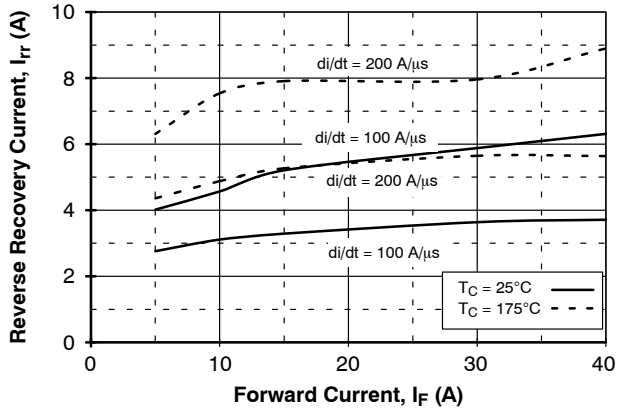


Figure 17. Reverse Recovery Current

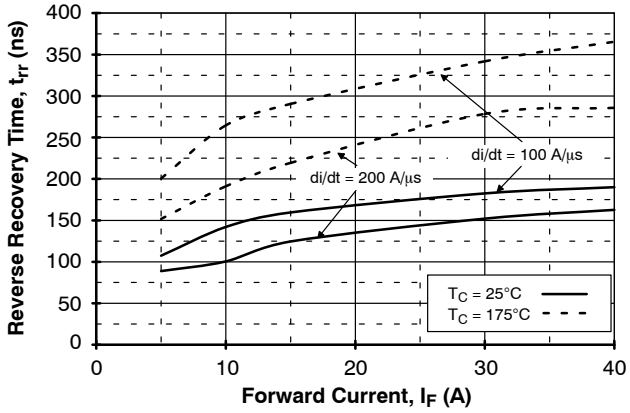


Figure 18. Reverse Recovery Time

TYPICAL CHARACTERISTICS

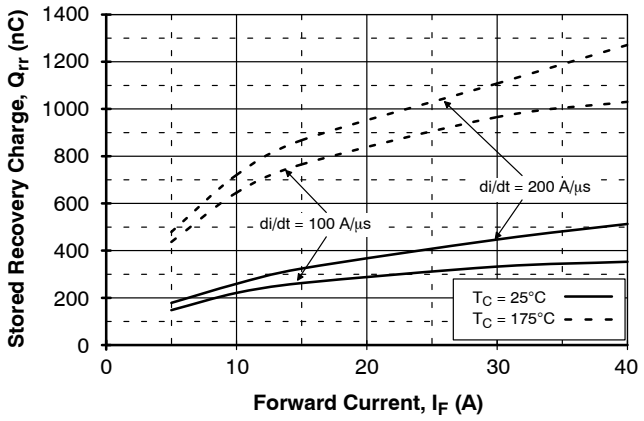


Figure 19. Stored Charge

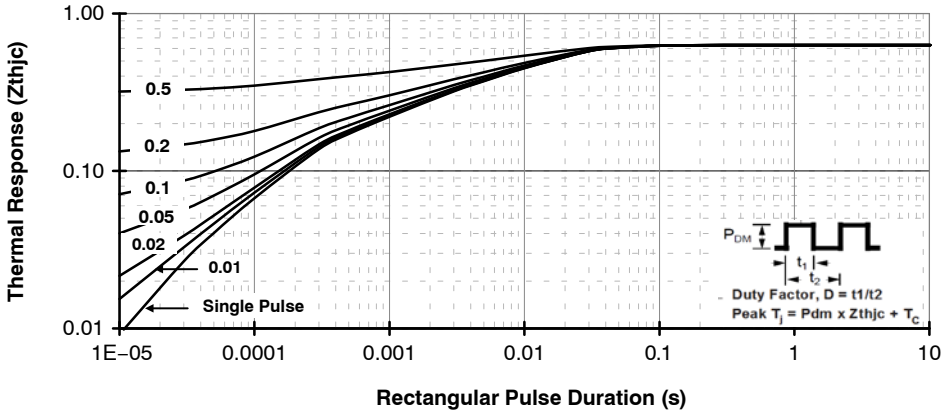


Figure 20. Transient Thermal Impedance of IGBT

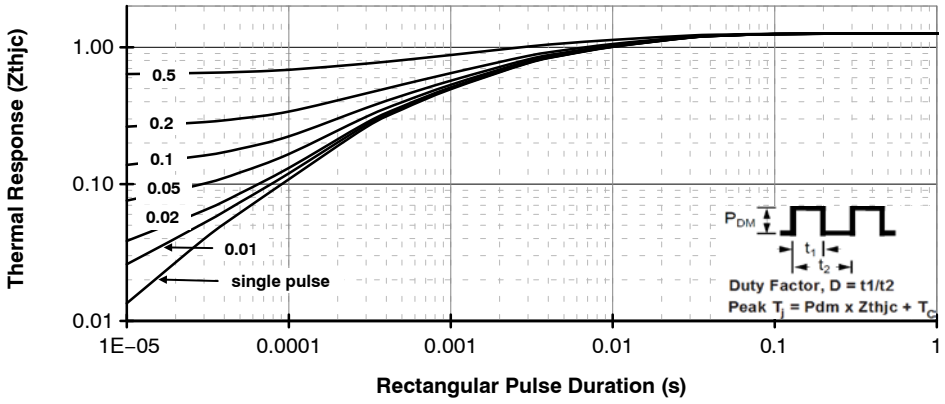
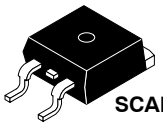


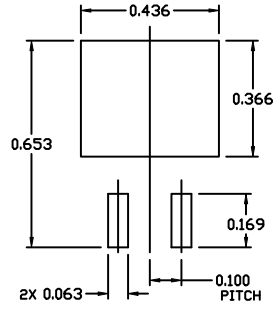
Figure 21. Transient Thermal Impedance of Diode

D²PAK–3 (TO–263, 3–LEAD)
CASE 418AJ
ISSUE F

DATE 11 MAR 2021



SCALE 1:1



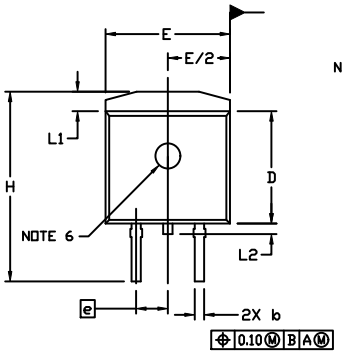
RECOMMENDED
MOUNTING FOOTPRINT

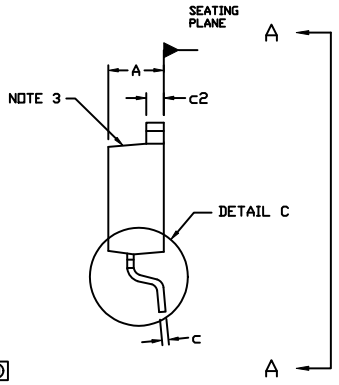
* For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

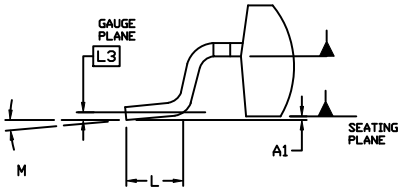
NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: INCHES
3. CHAMFER OPTIONAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.005 PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AT DATUM H.
5. THERMAL PAD CONTOUR IS OPTIONAL WITHIN DIMENSIONS E, L1, D1, AND E1.
6. OPTIONAL MOLD FEATURE.
7. ①, ② … OPTIONAL CONSTRUCTION FEATURE CALL OUTS.

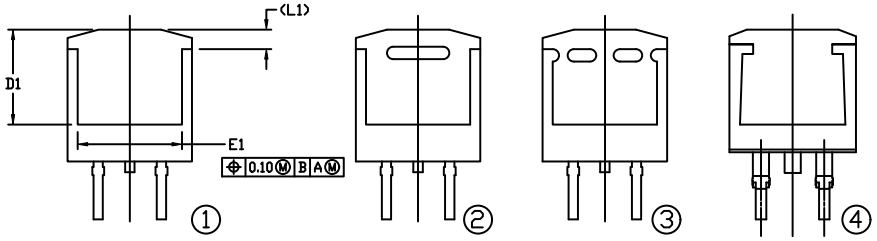
	INCHES		MILLIMETERS	
DIM	MIN.	MAX.	MIN.	MAX.
A	0.160	0.190	4.06	4.83
A1	0.000	0.010	0.00	0.25
b	0.020	0.039	0.51	0.99
c	0.012	0.029	0.30	0.74
c2	0.045	0.065	1.14	1.65
D	0.330	0.380	8.38	9.65
D1	0.260	---	6.60	---
E	0.380	0.420	9.65	10.67
E1	0.245	---	6.22	---
e	0.100 BSC		2.54 BSC	
H	0.575	0.625	14.60	15.88
L	0.070	0.110	1.78	2.79
L1	---	0.066	---	1.68
L2	---	0.070	---	1.78
L3	0.010 BSC		0.25 BSC	
M	0°	8°	0°	8°







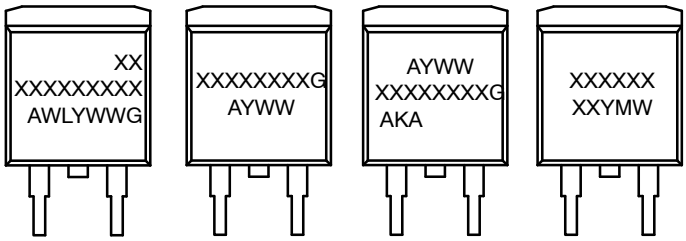
DETAIL C
TIP LEADFORM
ROTATED 90° CW



VIEW A–A

VIEW A–A
OPTIONAL CONSTRUCTIONS

GENERIC MARKING DIAGRAMS*



IC **Standard** **Rectifier** **SSG**

XXXXXX = Specific Device Code
A = Assembly Location
WL = Wafer Lot
Y = Year
WW = Work Week
W = Week Code (SSG)
M = Month Code (SSG)
G = Pb–Free Package
AKA = Polarity Indicator

*This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, “G” or microdot “ ▪”, may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	**D²PAK–3 (TO–263, 3–LEAD)**	**PAGE 1 OF 1**

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:
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